**Product data sheet** 

## 1. General description

PNP low  $V_{CEsat}$  transistor in a SOT457 (SC-74) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS303ND

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

## 3. Applications

- High-voltage DC-to-DC conversion
- · High-voltage MOSFET gate driving
- · High-voltage motor control
- · High-voltage power switches (e.g. motors, fans)
- · Thin Film Transistor (TFT) backlight inverter
- Automotive applications

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-60	V
Ic	collector current		[1]	-	-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	-6	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	75	100	mΩ

[1] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



60 V, 3 A PNP low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		C
2	С	collector	<u> </u>	
3	В	base		В
4	Е	emitter		E
5	С	collector	TSOP6 (SOT457)	sym030
6	С	collector		

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS303PD	TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS303PD	АН

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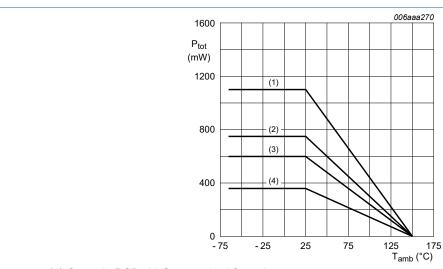
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-60	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current		[1]	-	-1	Α
			[2]	-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-6	Α
I <sub>B</sub>	base current			-	-800	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	360	mW
			[3]	-	600	mW
			[4]	-	750	mW
			[2]	-	1.1	W
			[1] [5]	-	2.5	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [5] Pulse test:  $t_p \le 10 \text{ ms}$ ;  $\delta \le 10 \%$ .



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (4) FR4 PCB, standard footprint

Fig. 1. Power derating curves

PBSS303PD

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance fr junction to ambient	thermal resistance from	[2] [3] [4]	[1]	-	-	350	K/W
	junction to ambient		[2]	-	-	208	K/W
			[3]	-	-	167	K/W
			[4]	-	-	113	K/W
			[1] [5]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	45	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Pulse test:  $t_p \le 10$  ms;  $\delta \le 10$  %.

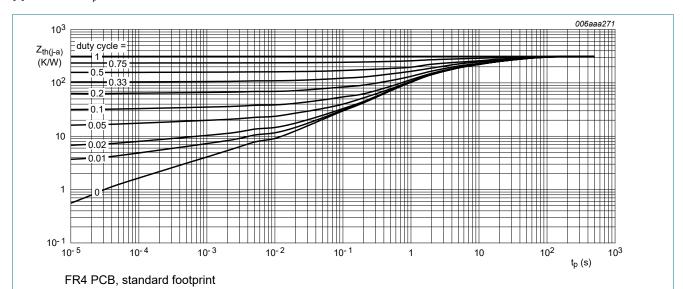


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

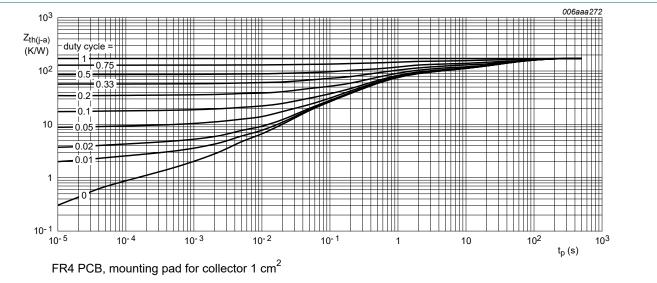


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

PBSS303PE

#### 60 V, 3 A PNP low VCEsat transistor

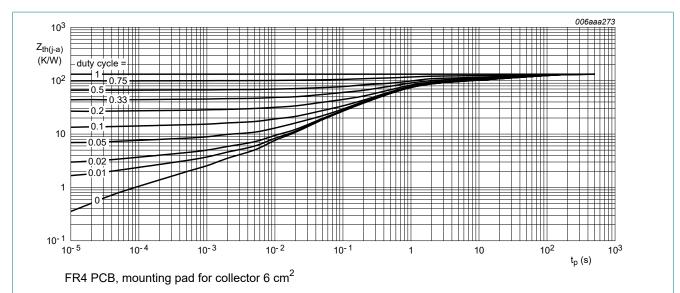


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

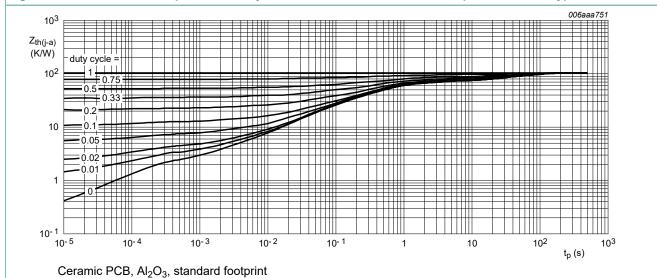


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
СВО	collector-base cut-off	V <sub>CB</sub> = -60 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -60 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
EBO	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
CES	collector-emitter cut-off current	V <sub>CE</sub> = -48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	180	265	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	160	235	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	130	185	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	95	135	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -4 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	60	80	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -5 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	35	50	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -6 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	20	30	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-55	-70	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-100	-135	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-150	-200	mV
		$I_C$ = -3 A; $I_B$ = -150 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-275	-365	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-210	-290	mV
		$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-285	-385	mV
		$I_C$ = -5 A; $I_B$ = -500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-375	-495	mV
		$I_C$ = -6 A; $I_B$ = -600 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-515	-675	mV
CEsat	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	75	100	mΩ
, BEsat	base-emitter saturation	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-0.78	-0.87	V
	voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-0.8	-0.89	V
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.83	-0.92	V
		$I_C$ = -3 A; $I_B$ = -150 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.92	-0.99	V
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-0.94	-1.02	V
/ <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -2 A; T <sub>amb</sub> = 25 °C	-	-0.8	-1	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d</sub>	delay time	V <sub>CC</sub> = -9.2 V; I <sub>C</sub> = -2 A; I <sub>Bon</sub> = -0.1 A; I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C	-	13	-	ns
t <sub>r</sub>	rise time		-	53	-	ns
t <sub>on</sub>	turn-on time		-	66	-	ns
ts	storage time		-	230	-	ns
t <sub>f</sub>	fall time		-	76	-	ns
t <sub>off</sub>	turn-off time		-	306	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	110	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_E$ = 0 A; $I_e$ = 0 A; $I_e$ = 1 MHz; $I_{CB}$ = 25 °C	-	58	-	pF

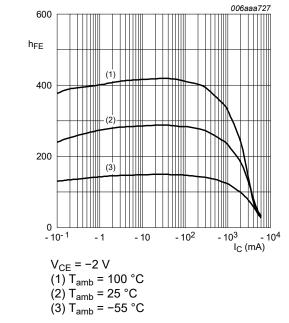


Fig. 6. DC current gain as a function of collector current; typical values

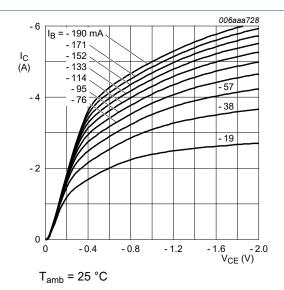


Fig. 7. Collector current as a function of collectoremitter voltage; typical values

### 60 V, 3 A PNP low VCEsat transistor

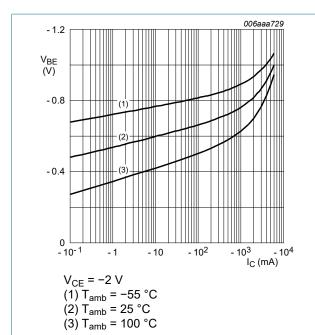


Fig. 8. Base-emitter voltage as a function of collector current; typical values

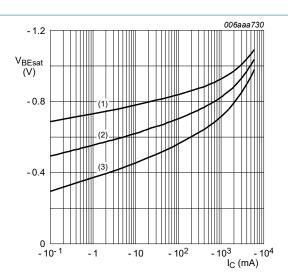


Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values

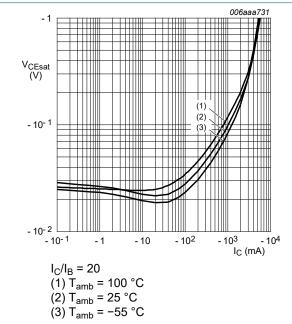


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

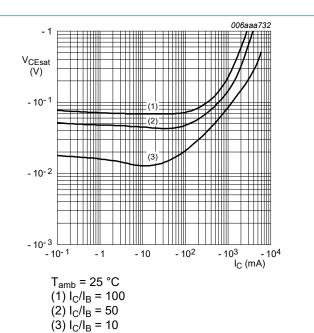


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values

**Product data sheet** 

### 60 V, 3 A PNP low VCEsat transistor

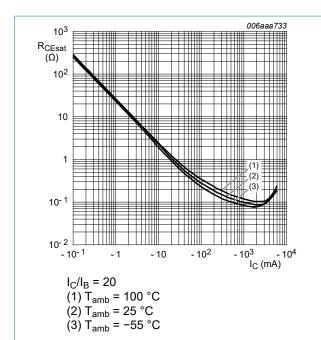


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

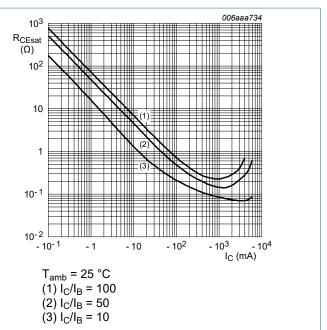


Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 3 A PNP low VCEsat transistor

## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

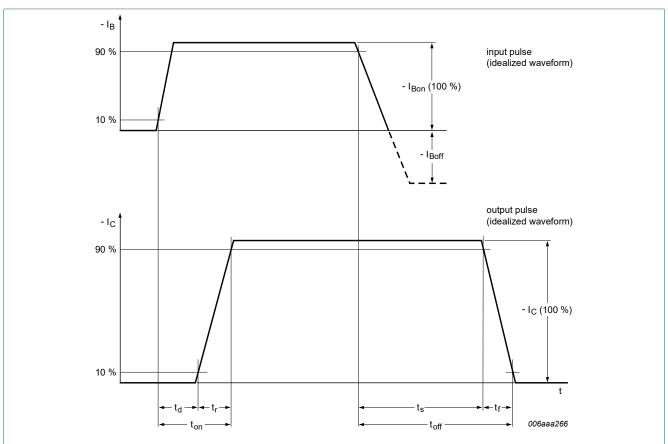


Fig. 14. Transistor switching time definition

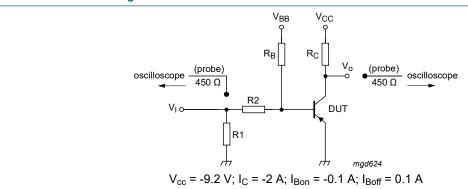
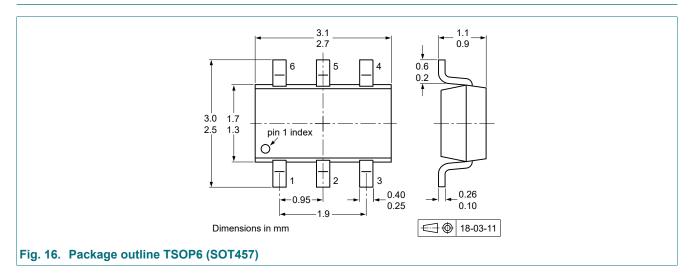


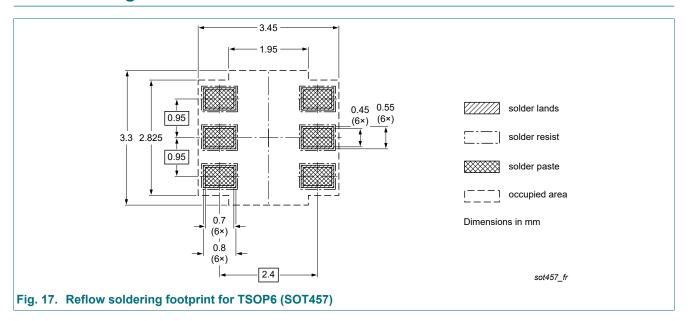
Fig. 15. Test circuit for switching times

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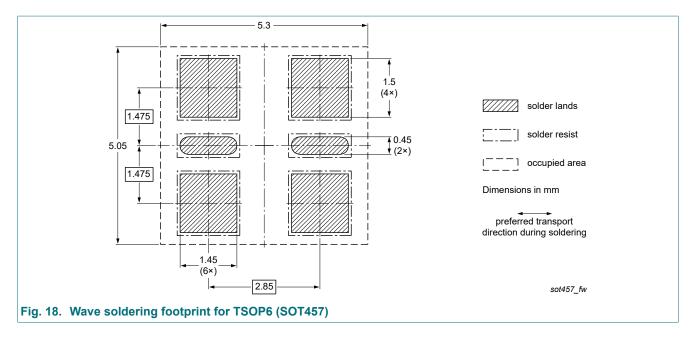
# 12. Package outline



# 13. Soldering



## 60 V, 3 A PNP low VCEsat transistor



## 60 V, 3 A PNP low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS303PD v.3	20230915	Product data sheet	-	PBSS303PD_2		
Modifications:	Nexperia. • Legal texts ha	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Section "Packing information" removed.</li> </ul>				
PBSS303PD_2	20091120	Product data sheet	-	PBSS303PD_1		
PBSS303PD_1	20060531	Product data sheet	-	-		

#### 60 V, 3 A PNP low VCEsat transistor

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## 60 V, 3 A PNP low VCEsat transistor

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 15 September 2023

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